

MOSFETs Silicon N-Channel MOS (DTMOSIV-H)

TK25N60X

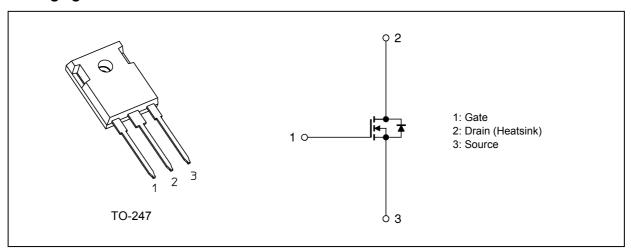
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.105 Ω (typ.) by used to Super Junction Structure : DTMOS
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode: V_{th} = 2.5 to 3.5 V (V_{DS} = 10 V, I_D = 1.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit		
Drain-source voltage			V_{DSS}	600	V
Gate-source voltage			V_{GSS}	±30	
Drain current (DC)		(Note 1)	I _D	25	Α
Drain current (pulsed)		(Note 1)	I _{DP}	100	
Power dissipation	(T _c = 25°C)		P _D	180	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	306	mJ
Avalanche current			I _{AR}	6.2	Α
Reverse drain current (DC)		(Note 1)	I _{DR}	25	
Reverse drain current (pulsed)		(Note 1)	I _{DRP}	100	
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.694	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 13.9 mH, R_{G} = 25 $\Omega,$ I_{AR} = 6.2 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1.2 mA	2.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 7.5 A	ı	0.105	0.125	Ω

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	2400	_	pF
Reverse transfer capacitance	C_{rss}		_	6		
Output capacitance	C _{oss}		_	60	_	
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	100	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	1.7	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	15	_	ns
Switching time (turn-on time)	t _{on}		_	45	_	
Switching time (fall time)	t _f		_	4	_	
Switching time (turn-off time)	t _{off}		_	90	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 12.5 A	50	_	_	V/ns

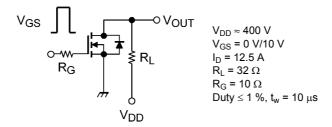


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_{g}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 25 \text{ A}$		40	1	nC
Gate-source charge 1	Q _{gs1}		_	14	_	
Gate-drain charge	Q_{gd}		_	15		

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 25 A, V _{GS} = 0 V	1	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 12.5 A, V _{GS} = 0 V		400	_	ns
Reverse recovery charge	Q_{rr}	-dI _{DR} /dt = 50 A/μs	_	3.3	_	μС
Peak reverse recovery current	I _{rr}		1	16.5	_	Α
Diode dv/dt ruggedness	dv/dt	I_{DR} = 12.5 A, V_{GS} = 0 V, V_{DD} = 400 V	15	_	_	V/ns



7. Marking (Note)

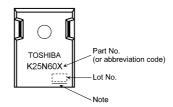


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS

compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the

restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

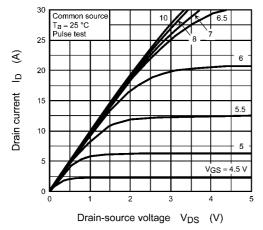
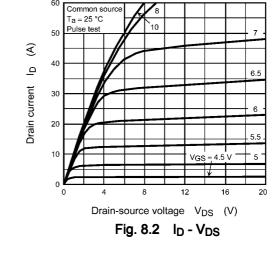


Fig. 8.1 I_D - V_{DS}



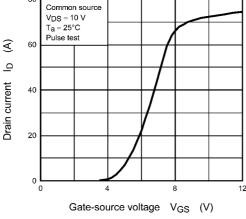


Fig. 8.3 I_D - V_{GS}

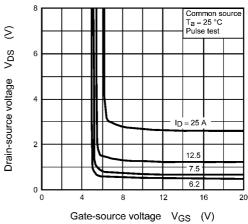


Fig. 8.4 V_{DS} - V_{GS}

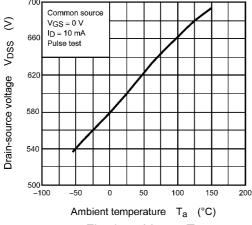


Fig. 8.5 V_{DSS} - T_a

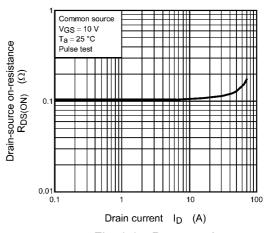


Fig. 8.6 $R_{DS(ON)}$ - I_D

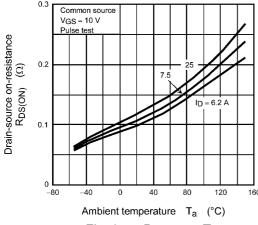
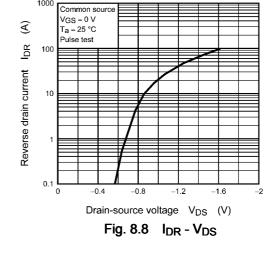


Fig. 8.7 R_{DS(ON)} - T_a



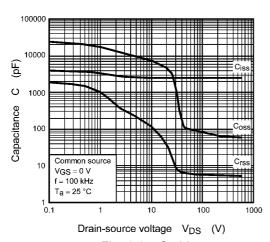


Fig. 8.9 C - V_{DS}

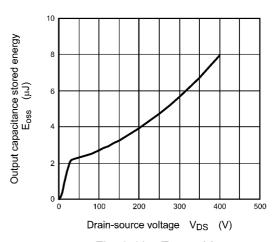


Fig. 8.10 E_{OSS} - V_{DS}

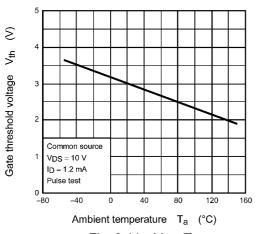


Fig. 8.11 V_{th} - T_a

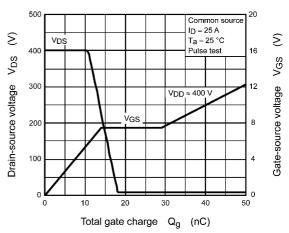


Fig. 8.12 Dynamic Input/Output Characteristics

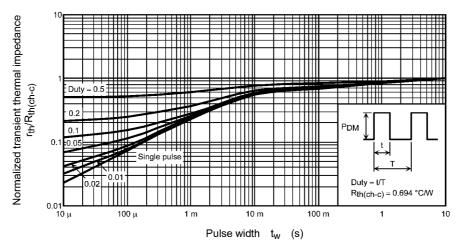


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

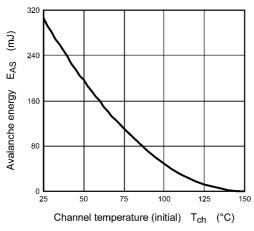


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

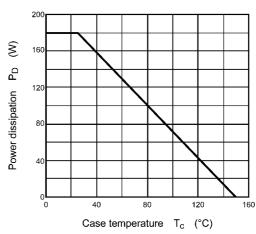


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

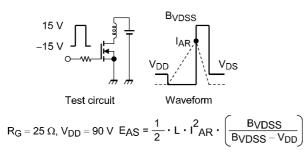


Fig. 8.16 Test Circuit/Waveform

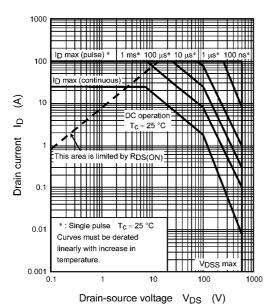


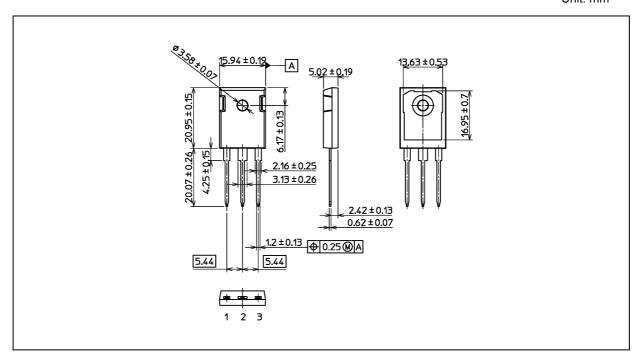
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)
JEITA: SC-65
TOSHIBA: 2-16L1A
Nickname: TO-247



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